

2 Transistors

2.2 RF-MOSFET

Toshiba's RF-MOSFETs are ideal for RF power amplifier applications.

Features

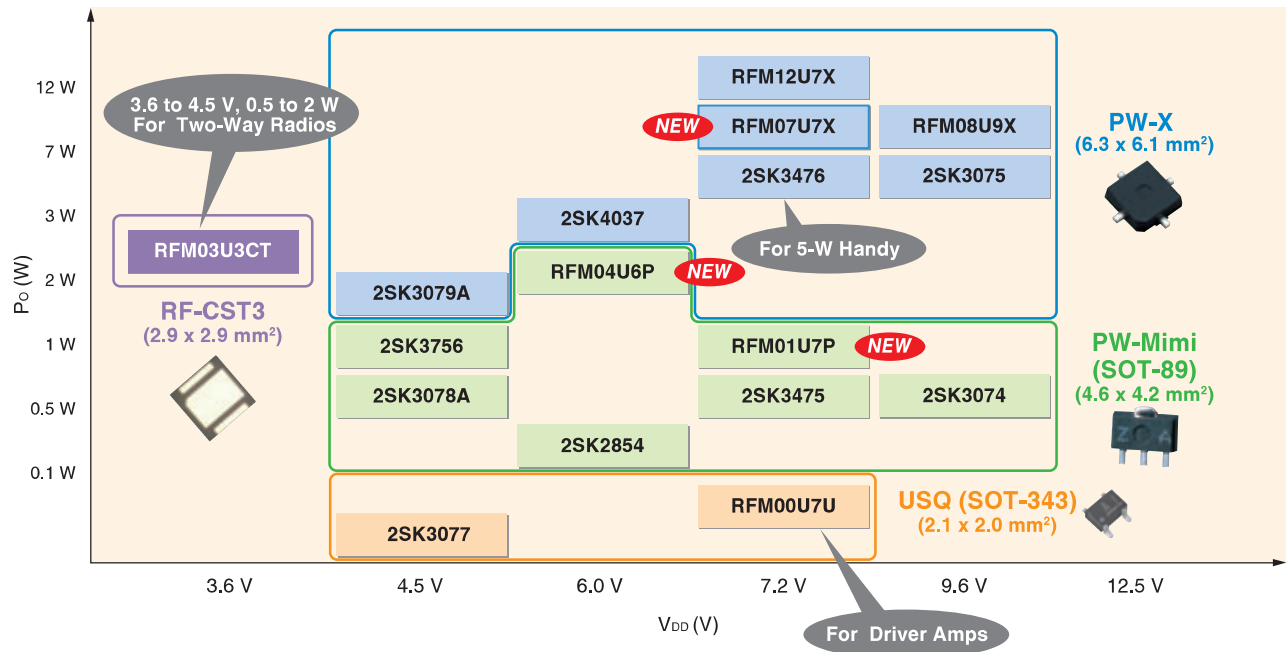
1. Wide Lineup

Available with output power up to 12 W and supply voltage from 3.6 V to 12.5 V for final and driver amplifier applications.

2. Maximum output load mismatch of 20:1 (all phase)

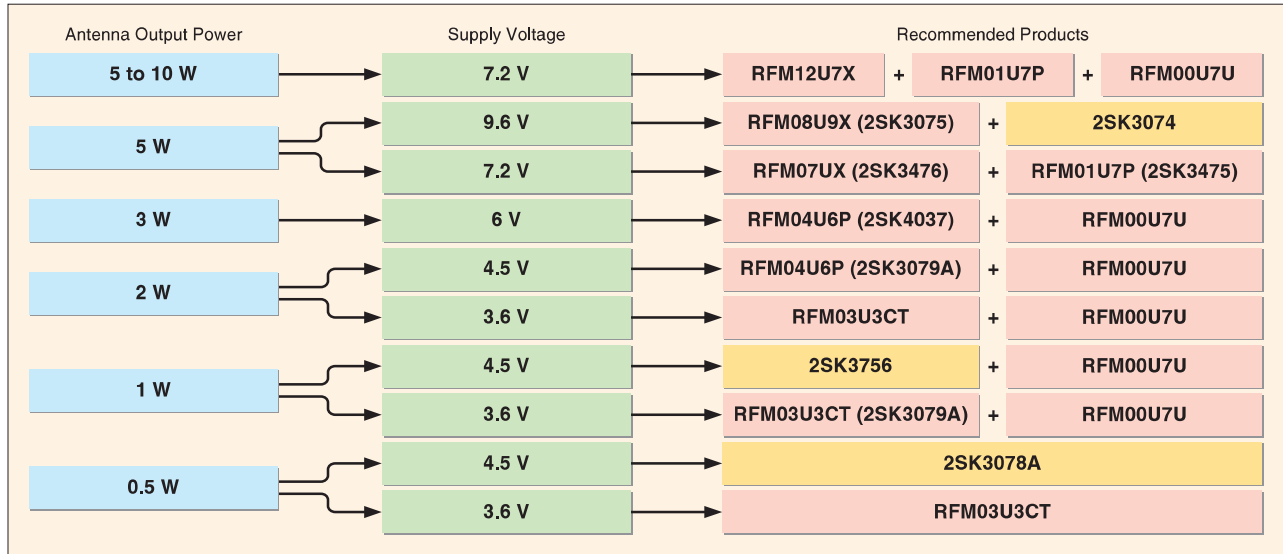
Toshiba's RF-MOSFETs can be used as the final amp.

RF-MOSFET Lineup





Selection Guide



 : New product

Selection Table

Applications	Part Number	Absolute Maximum Ratings (Tc = 25°C)			Min	Pc (W)			Package
		V _{DSS} (V)	P _D (W)	I _D (A)		Test Conditions			
						V _{DD} (V)	f (MHz)	P _i (W)	
UHF/VHF Professional radios Amateur radios	RFM12U7X	20	20	4	11.5	7.2	520	1.0	PW-X
	RFM08U9X	36	20	5	7.5	9.6	520	0.5	PW-X
	2SK3075	30	20	5	7.5	9.6	520	0.5	PW-X
	2SK3476	20	20	3	7	7.2	520	0.5	PW-X
	2SK3074	30	3	1	0.63	9.6	520	0.02	PW-Mini
	RFM03U3CT	16	7	2.5	2.3	3.6	520	0.1	RF-CST3
	2SK3475	20	3	1	0.63	7.2	520	0.02	PW-Mini
	RFM01U7P	20	3	1	1.0	7.2	520	0.1	PW-Mini
FRS/GMRS	2SK2854	10	0.5	0.5	0.2	6	849	0.02	PW-Mini
	2SK4037	12	20	3	3.55	6	470	0.3	PW-X
	RFM04U6P	16	7	2	3.5	6.0	470	0.2	PW-Mini
	2SK3079A	10	20	3	2.24	4.5	470	0.1	PW-X
	2SK3756	7.5	3	1	1.26	4.5	470	0.1	PW-Mini
Drivers	2SK3078A	10	3	0.5	0.63	4.5	470	0.1	PW-Mini
	2SK3077	10	0.25	0.1	0.032	4.8	915	0.001	USQ
	RFM00U7U	20	0.25	0.1	0.1	7.2	520	0.01	USQ

 : New product

2.3 Dual-Gate MOSFET

Selection Table

Applications	Part Number	Absolute Maximum Ratings			Electrical Characteristics											Package	
		V _{DS} (V)	I _D (mA)	P _D (mW)	I _{DSS} Max			I _{YfsI} Typ.			G _{ps} /NF Typ.						
					V _{DS} (V)	V _{G1S} /V _{G2S} (V)	@1kHz (mS)	V _{DS} (V)	I _D (mA)	V _{G2S} (V)	(dB/dB)	V _{DS} (V)	I _D (mA)	V _{G2S} (V)	f (MHz)		
		(V)	(mA)	(mW)	(mA)	(V)	(V)	(mS)	(V)	(mA)	(V)	(dB/dB)	(V)	(mA)	(V)		(MHz)
VHF RF, MIX	3SK292	12.5	30	150	0.1	6	0/4.5	23.5	6	10	4.5	26.0/1.4	6	10	4.5	500	SMQ
	100			USQ													
UHF RF, MIX	3SK291	12.5	30	150	0.1	6	0/4.5	26.0	6	10	4.5	22.5/1.5	6	10	4.5	800	SMQ
	100			USQ													